

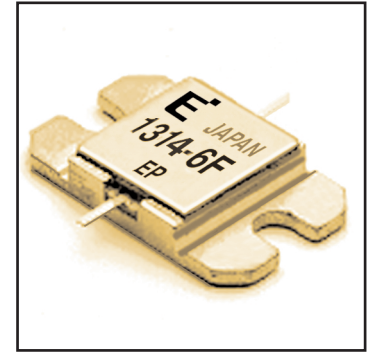
### FEATURES

- High Output Power:  $P_{1dB} = 37.5dBm$  (Typ.)
- High Gain:  $G_{1dB} = 5.5dB$  (Typ.)
- High PAE:  $\eta_{add} = 22\%$  (Typ.)
- Broad Band: 13.75 ~ 14.5GHz
- Impedance Matched  $Z_{in}/Z_{out} = 50\Omega$
- Hermetically Sealed

### DESCRIPTION

The FLM1314-6F is a power GaAs FET that is internally matched for standard communication bands to provide optimum power and gain in a 50 ohm system.

Eudyna's stringent Quality Assurance Program assures the highest reliability and consistent performance.



### ABSOLUTE MAXIMUM RATING (Ambient Temperature $T_a=25^\circ C$ )

Item	Symbol	Condition	Rating	Unit
Drain-Source Voltage	$V_{DS}$		15	V
Gate-Source Voltage	$V_{GS}$		-5	V
Total Power Dissipation	$P_T$	$T_C = 25^\circ C$	31.2	W
Storage Temperature	$T_{stg}$		-65 to +175	$^\circ C$
Channel Temperature	$T_{ch}$		175	$^\circ C$

Fujitsu recommends the following conditions for the reliable operation of GaAs FETs:

1. The drain-source operating voltage ( $V_{DS}$ ) should not exceed 10 volts.
2. The forward and reverse gate currents should not exceed 26.0 and -2.8 mA respectively with gate resistance of 100 $\Omega$ .

### ELECTRICAL CHARACTERISTICS (Ambient Temperature $T_a=25^\circ C$ )

Item	Symbol	Test Conditions	Limit			Unit
			Min.	Typ.	Max.	
Saturated Drain Current	$I_{DSS}$	$V_{DS} = 5V, V_{GS} = 0V$	-	2800	4200	mA
Transconductance	$g_m$	$V_{DS} = 5V, I_{DS} = 1800mA$	-	2350	-	mS
Pinch-off Voltage	$V_p$	$V_{DS} = 5V, I_{DS} = 120mA$	-0.5	-1.5	-3.0	V
Gate Source Breakdown Voltage	$V_{GSO}$	$I_{GS} = -120\mu A$	-5.0	-	-	V
Output Power at 1dB G.C.P.	$P_{1dB}$	$V_{DS} = 10V,$ $I_{DS} = 0.6 I_{DSS}$ (Typ.), $f = 13.75 \sim 14.5$ GHz, $Z_S = Z_L = 50$ ohm	36.5	37.5	-	dBm
Power Gain at 1dB G.C.P.	$G_{1dB}$		5.0	5.5	-	dB
Drain Current	$I_{dsr}$		-	1800	2100	mA
Power-added Efficiency	$\eta_{add}$		-	22	-	%
Gain Flatness	$\Delta G$		-	-	$\pm 0.6$	dB
3rd Order Intermodulation Distortion	$IM_3$	$f = 14.5GHz, \Delta f = 10$ MHz 2-Tone Test $P_{out} = 26.5dBm$ S.C.L.	-42	-45	-	dBc
Thermal Resistance	$R_{th}$	Channel to Case	-	4.0	4.5	$^\circ C/W$
Channel Temperature Rise	$\Delta T_{ch}$	$10V \times I_{dsr} \times R_{th}$	-	-	80	$^\circ C$

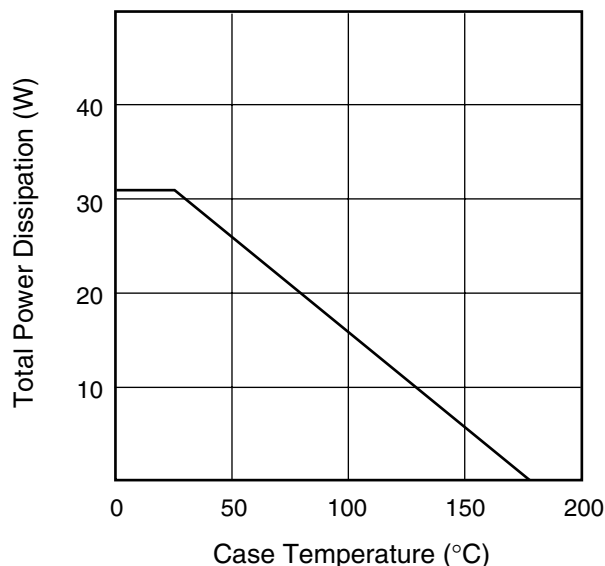
CASE STYLE: IA

G.C.P.: Gain Compression Point, S.C.L.: Single Carrier Level

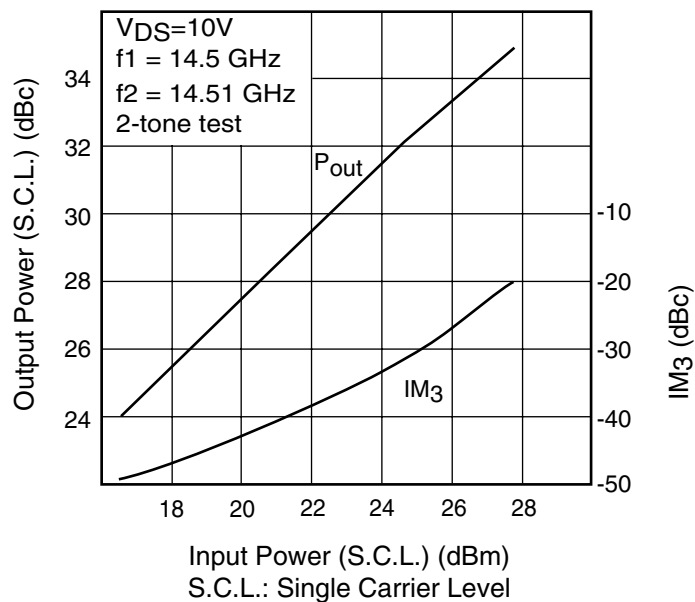
# FLM1314-6F

X, Ku-Band Internally Matched FET

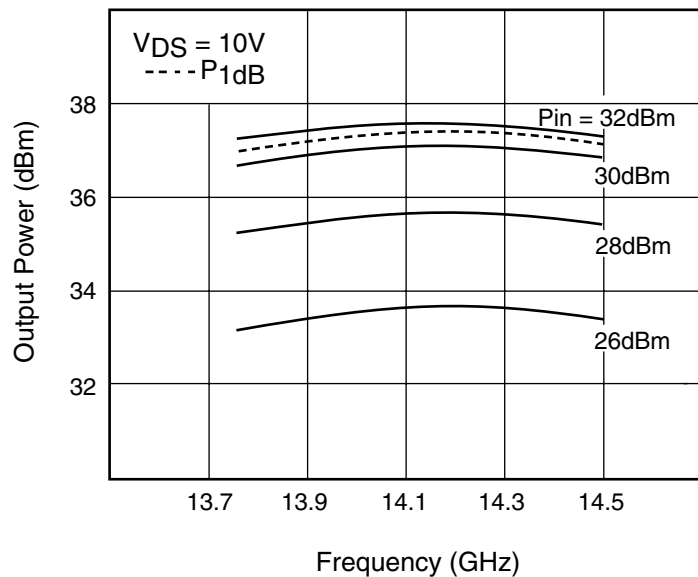
POWER DERATING CURVE



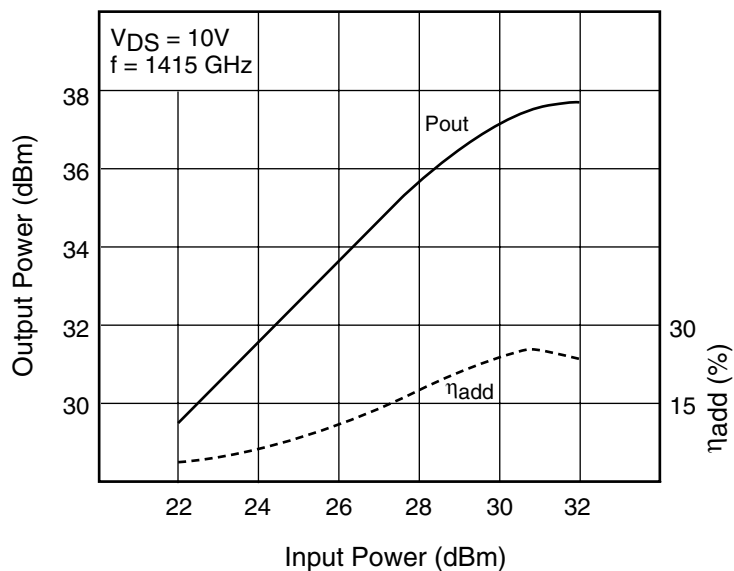
OUTPUT POWER & IM<sub>3</sub> vs. INPUT POWER

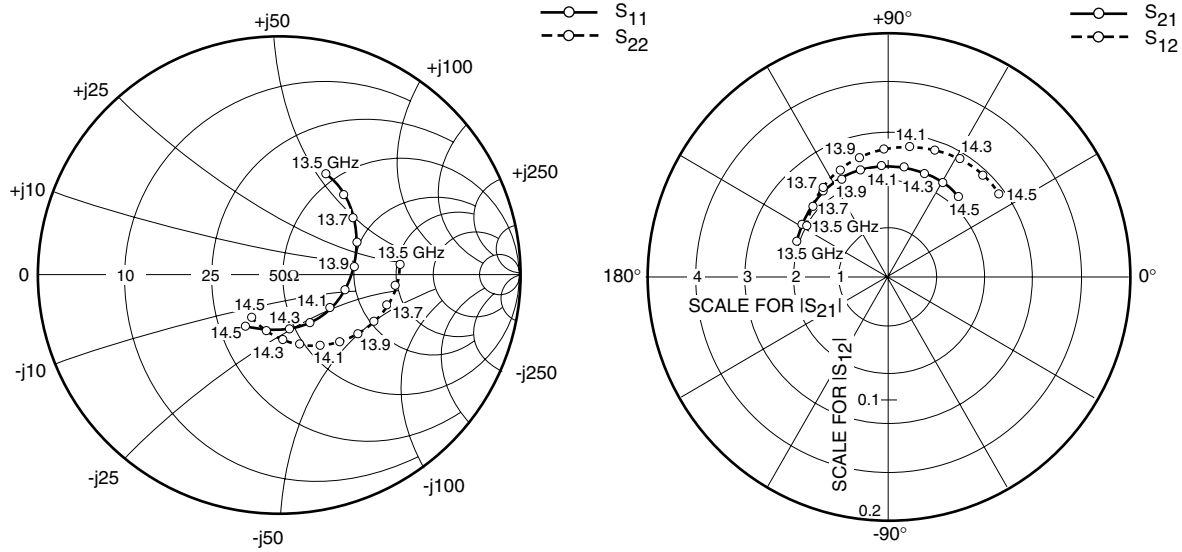


OUTPUT POWER vs. FREQUENCY



OUTPUT POWER vs. INPUT POWER





### S-PARAMETERS

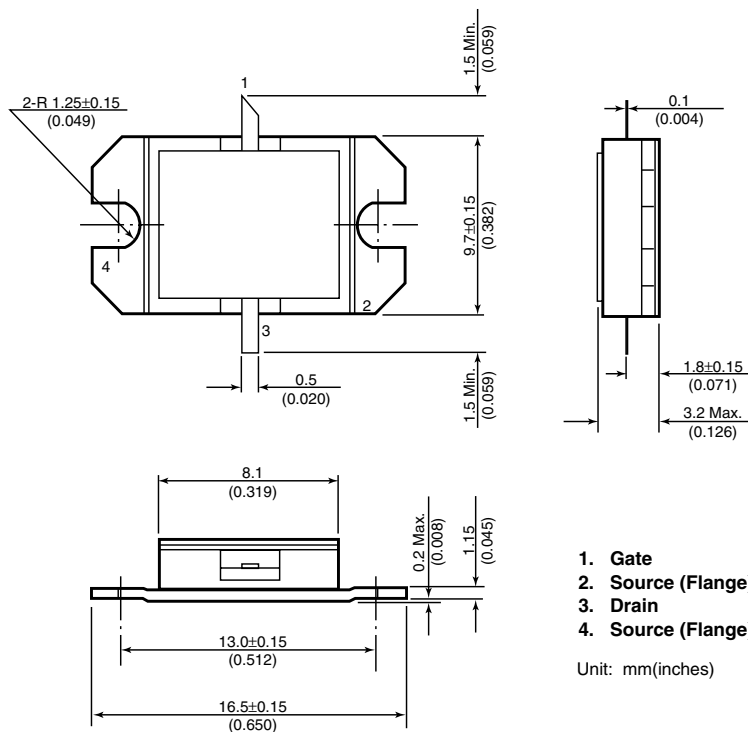
$V_{DS} = 10V$ ,  $I_{DS} = 1800mA$

FREQUENCY (MHZ)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
13500	.467	64.7	2.029	159.9	.080	148.2	.500	5.2
13600	.432	51.8	2.085	149.3	.085	137.4	.482	-5.2
13700	.393	37.8	2.143	138.5	.091	126.7	.465	-15.9
13800	.356	22.9	2.191	127.5	.096	114.5	.440	-26.8
13900	.319	6.2	2.226	116.3	.101	103.8	.413	-37.2
14000	.283	-12.0	2.255	105.2	.106	92.5	.379	-48.3
14100	.256	-32.6	2.266	93.9	.109	81.3	.344	-59.7
14200	.234	-55.5	2.267	82.4	.111	70.2	.307	-72.7
14300	.232	-78.9	2.251	71.1	.114	59.1	.271	-86.9
14400	.237	-101.4	2.219	59.9	.114	47.2	.240	-102.9
14500	.252	-122.2	2.176	48.8	.114	37.2	.214	-121.4

# FLM1314-6F

## X, Ku-Band Internally Matched FET

### Case Style "IA" Metal-Ceramic Hermetic Package



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#### CAUTION

Eudyna Devices Inc. products contain **gallium arsenide (GaAs)** which can be hazardous to the human body and the environment. For safety, observe the following procedures:

- Do not put this product into the mouth.
- Do not alter the form of this product into a gas, powder, or liquid through burning, crushing, or chemical processing as these by-products are dangerous to the human body if inhaled, ingested, or swallowed.
- Observe government laws and company regulations when discarding this product. This product must be discarded in accordance with methods specified by applicable hazardous waste procedures.

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